Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-4 (canceled)

Claim 5 (currently amended): A power semiconductor element, comprising:

an emitter region; and

a stop zone in front of said emitter region, $[[\dot{\tau}]]$

said emitter region and said-stop zone having mutually opposite conductivities; and

said stop zone having foreign atoms with at least one energy level within the band gap of the semiconductor and at least 200 meV away from both a conduction band and a valence band of the semiconductor, resulting in said stop zone being only partially electrically active in the on-state and fully electrically active in the off-state for carriers emitted by the emitter region, said stop zone and said emitter region having mutually opposite conductivities.

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Claim 6 (canceled)

Claim 7 (previously presented): The power semiconductor element of claim 5, wherein said foreign atoms are sulfur atoms.

Claim 8 (previously presented): The power semiconductor element of claim 5, wherein said foreign atoms are selenium atoms.